

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair
- **Lead Free/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3 and 4)**
- **Qualified to AEC-Q101 Standards for High Reliability**

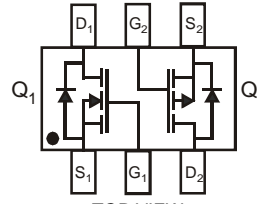


TOP VIEW

SOT-363

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.008 grams (approximate)


 TOP VIEW
Internal Schematic

Maximum Ratings – Total Device @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Power Dissipation (Note 1)	P _D	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Maximum Ratings N-CHANNEL – Q₁, 2N7002 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ	V _{DGR}	60	V
Gate-Source Voltage	V _{GSS}	±20 ±40	V
Drain Current (Note 1)	I _D	Continuous	115
		Continuous @ 100°C	73
		Pulsed	800

Maximum Ratings P-CHANNEL – Q₂, BSS84 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-50	V
Drain-Gate Voltage R _{GS} ≤ 20KΩ	V _{DGR}	-50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 1)	I _D	-130	mA

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

Electrical Characteristics N-CHANNEL – Q₁, 2N7002 Section @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	70	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V @ T _C = 25°C @ T _C = 125°C
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.2 4.4	7.5 13.5	Ω	V _{GS} = 5.0V, I _D = 0.05A @ T _J = 25°C @ T _J = 125°C
On-State Drain Current	I _{D(ON)}	0.5	1.0	—	A	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance	g _{FS}	80	—	—	mS	V _{DS} = 10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	22	50	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	11	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.0	5.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	7.0	20	ns	V _{DD} = 30V, I _D = 0.2A,
Turn-Off Delay Time	t _{D(OFF)}	—	11	20	ns	R _L = 150Ω, V _{GEN} = 10V, R _{GEN} = 25Ω

Electrical Characteristics P-CHANNEL – Q₂, BSS84 Section @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-15 -60 -100	μA μA nA	V _{DS} = -50V, V _{GS} = 0V, T _J = 25°C V _{DS} = -50V, V _{GS} = 0V, T _J = 125°C V _{DS} = -25V, V _{GS} = 0V, T _J = 25°C
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	-0.8	—	-2.0	V	V _{DS} = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	10	Ω	V _{GS} = -5V, I _D = -0.100A
Forward Transconductance	g _{FS}	.05	—	—	S	V _{DS} = -25V, I _D = -0.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	45	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	10	—	ns	V _{DD} = -30V, I _D = -0.27A,
Turn-Off Delay Time	t _{D(OFF)}	—	18	—	ns	R _{GEN} = 50Ω, V _{GS} = -10V

Notes: 5. Short duration pulse test used to minimize self-heating effect.

N-CHANNEL – 2N7002 SECTION

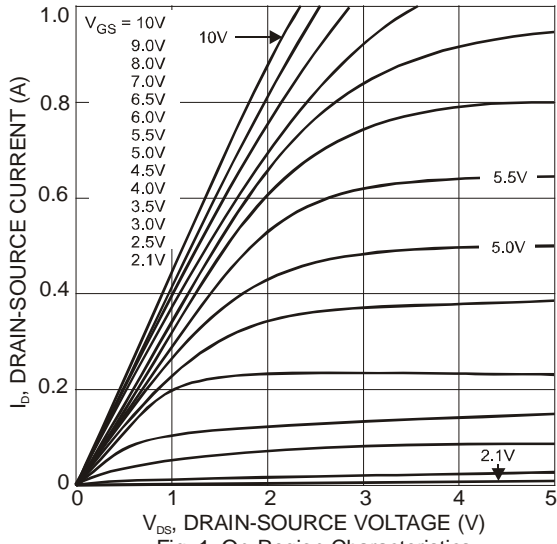


Fig. 1 On-Region Characteristics

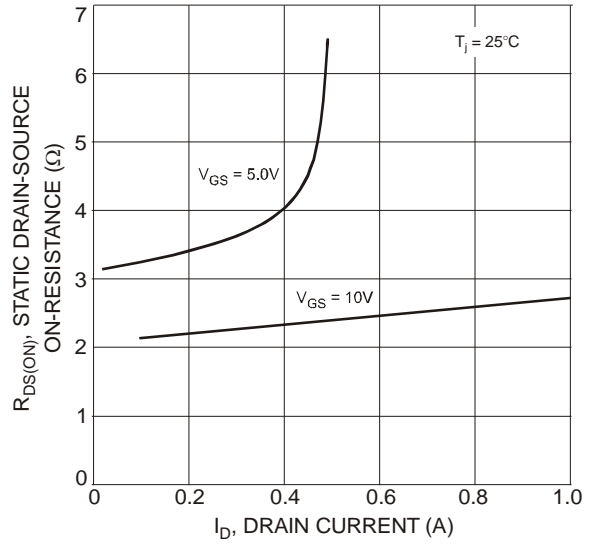


Fig. 2 On-Resistance vs. Drain Current

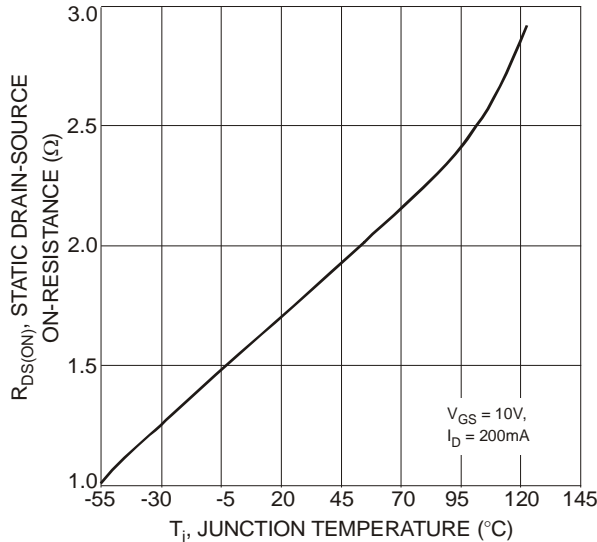


Fig. 3 On-Resistance vs. Junction Temperature

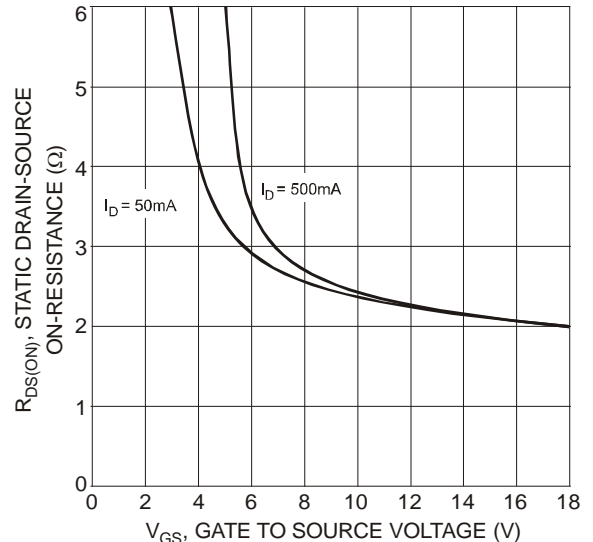


Fig. 4 On-Resistance vs. Gate-Source Voltage

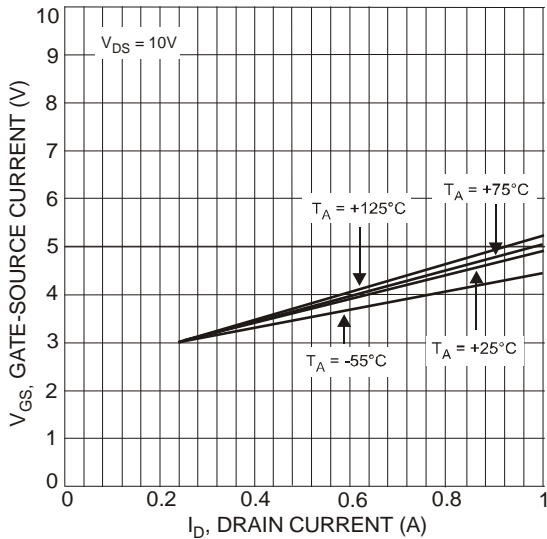


Fig. 5 Typical Transfer Characteristics

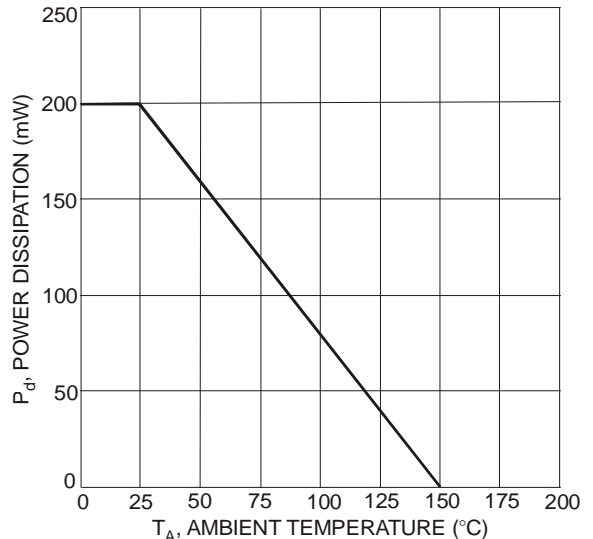


Fig. 6 Max Power Dissipation vs. Ambient Temperature

P-CHANNEL – BSS84 SECTION

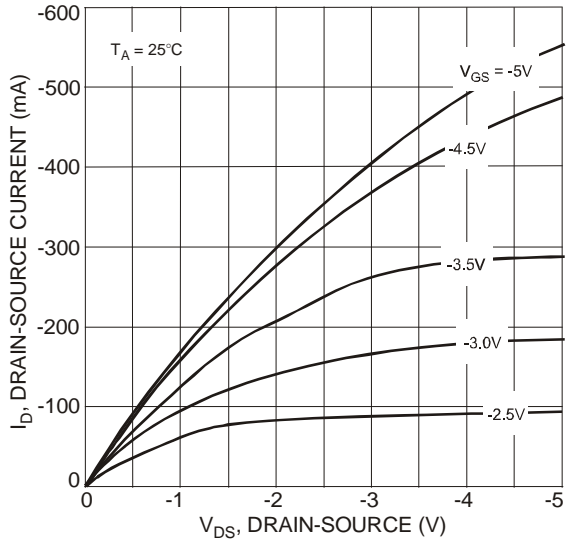


Fig. 7 Drain-Source Current vs. Drain-Source Voltage

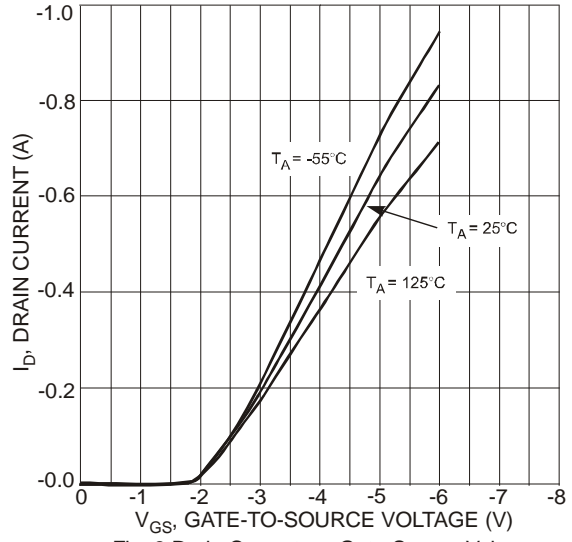


Fig. 8 Drain Current vs. Gate-Source Voltage

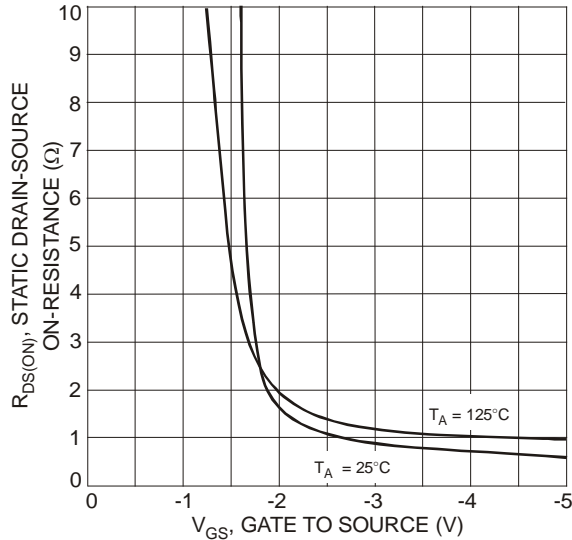


Fig. 9 On-Resistance vs. Gate-Source Voltage

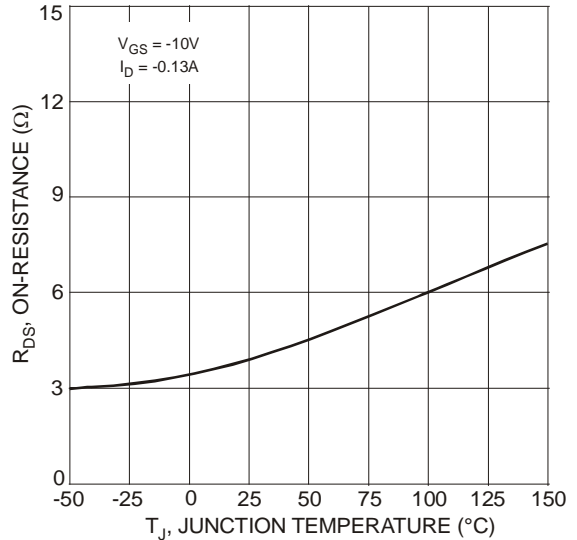


Fig. 10 On-Resistance vs. Junction Temperature

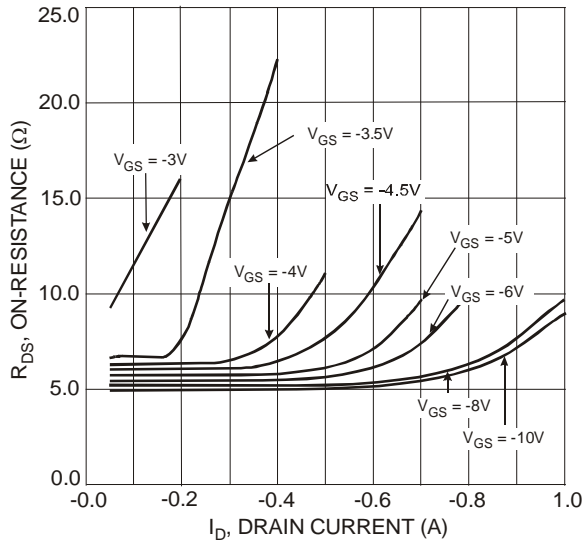


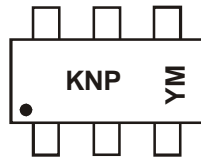
Fig. 11 On-Resistance vs. Drain Current

Ordering Information (Note 6)

Part Number	Case	Packaging
BSS8402DW-7-F	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



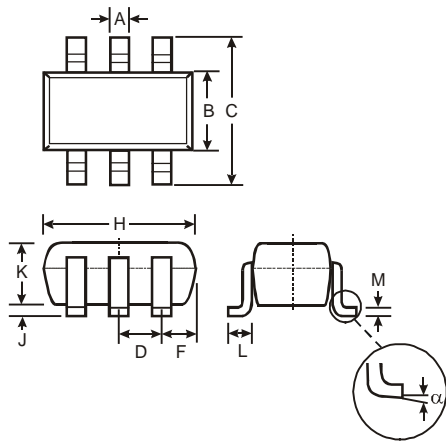
KNP = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: R = 2004)
 M = Month (ex: 9 = September)

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	P	R	S	T	U	V	W	X	Y	Z

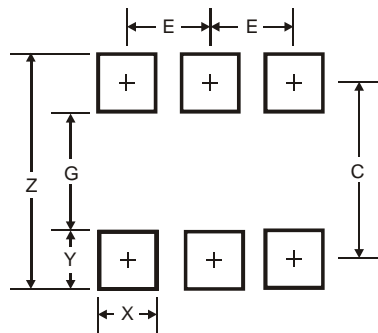
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C	1.9
E	0.65

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